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U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.		<del></del>		
OIPE				M-11822 US 09/925,10				
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant(s)				
(Use several sheets if necessary)					Jack H. Yuan et al.			
U.S. Patent Documents					Filing Date		Group	
AL AND	Bes				August 8, 2001		2185	
		,	U.S. P	atent Documents				
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing I	
BID	AA	5,043,940	Aug. 27, 1991	Harari	-			·
Bio	AB	5,070,032	Dec. 3, 1991	Yuan et al.				
PTo	AC	5,095,344	Mar. 10, 1992	Harari				
E.C.	AD	5,172,338	Dec. 15, 1992	Mehrotra et al.				<del></del> -
60	AE	5,297,148	Mar. 22, 1994	Harari et al.	<u> </u>			
Ho	AF	5,313,421	May 17, 1994	Guterman et al.				
No	AG	5,315,541	May 24, 1994	Harari et al.	T			
OTO	AH	5,343,063	Aug. 30, 1994	Yuan et al.	† <del></del>			_
130	ΑI	5,661,053	Aug. 26, 1997	Yuan				
1976	AJ	5,712,180	Jan. 27, 1998	Guterman et al.			·	
OTI	AK	6,103,573	Aug. 15, 2000	Harari et al.	-			
	.1		Foreign	Patent Documents	· · · · · · · · · · · · · · · · · · ·			
***							Trans	slation
<del></del>		Document	Date	Country	Class	Subclass	Yes	No
· · · · · · · · · · · · · · · · · · ·		•		<del>\</del>				<b> </b>
	<u></u>	OTHER AF	T (Including Au	ithor, Title, Date, Pertin	ent Pages,	Etc.)		<u>,                                    </u>
B	AL	Aritome, Seiichi,	'Advanced Flash International Elec	Memory Technology and tronic Devices Meeting,	Trends for	File Storage Ap		
WPO	AM Takeuchi, Y., et al., "A Self-Aligned STI Process Integration for Low Cost and Highly Reliable 1Gbit Flash Memories," 1998 Symposium on VLSI Technology; Digest of Technical Papers, IEEE, Honolulu, Hawaii, June 9-11, 1998, pp. 102-103.							
1550	AN	Lee, Jae-Duk, et al., "Effects of Parasitic Capacitance on NAND Flash Memory Cell Operation," Non-Volatile Semiconductor Memory Workshop, IEEE, Monterey, California, August 12-16, 2001, pp. 90-92.						
AO Chan, et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device, " IEEE Electron Device Letters, Vol. EDL-8, No. 3, March 1987, pp. 93-95.								
Examiner B	w L	Su	Date Considered	07/24/	05			
				citation is in conformand py of this form with your				

Sheet 2 of 2

								Sneet	
U.S. Department of Commerce, Patent and Trademark Office				Atty Dock	Atty Docket No.		Serial No.		
				M-11822	M-11822 US		09/925,102		
O INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant	Applicant(s)				
(Use several sheets if necessary)					Jack H. Y	Jack H. Yuan et al.			
D JUL 2 1 2003 W					Filing Dat	Filing Date		Group	
E.						August 8, 2001		2185	
RADEN			U.S. P	atent Documents					
*Examiner Document					Class	Subclass	Filing If Appro		
60	AP	6,151,248	Nov. 21, 2000	Harari et al.					
BOD	AQ	6,222,762	Apr. 24, 2001	Guterman et al.				-7	
			-						
		-	Foreign	Patent Documents			<u></u>		
							Tran	slation	
		Document	Date	Country	Class	Subclass	Yes	No	
								†	
		OTHER AR	RT (Including Au	thor, Title, Date, Per	tinent Pages, 1	Etc.)		<u>.l</u>	
OTO	AR	Nozaki et al., "A 1	-Mb EEPROM w	vith MONOS Memory s, Vol. 26, No. 4, April	Cell for Semic	onductor Disk	Application,	<b>3</b> )	
Б.	AS .	Eitan et al., "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell," <i>IEEE Electron Device Letters</i> , Vol. 21, No. 11, November 2000, pp. 543-545.							
Blo	AT	DiMaria et al., "Electrically-alterable read-only-memory using Si-rich SIO <sub>2</sub> injectors and a floating polycrystalline silicon storage layer," <i>J. Appl. Phys.</i> 52(7), July 1981, pp. 4825-4842.							
650	AU	Hori et al., "A MOSFET with Si-implanted Gate-Si0 <sub>2</sub> Insulator for Nonvolatile Memory Applications," IEDM 92, April 1992, pp. 469-472.							
Examiner $\mathcal{B}_c$	2	~ lo	Date Considered	07/24/00					
EXAMINER:	Initial if conform	reference considerenance and not consider	ed, whether or not dered. Include cop	citation is in conformation of this form with yo	ance with MPE our communica	P 609; Draw li tion to applican	ne through it.		

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

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Attorney Docket Number	6115-58351-01
Application Number	09/925,125
Filing Date	August 9, 2001
First Named Inventor	Scheurich
Art Unit	2171
Examiner Name	Unknown

## **U.S. PATENT DOCUMENTS**

NOTE: If this application was filed after June 30, 2003, copies of United States patents and United States published patent applications do not have to be provided to the Patent Office. This requirement of 37 C.F.R. § 1.98(a)(2)(i) has been waived by the United States Patent and Trademark Office pursuant to the Official Gazette Notice on August 5, 2003 (1276 OG 55).

	Official Gaz	zette Notice on August 5, 2003 (1:	276 OG 55).	
Examiner's Initials*	Cite No. (optional)	Number	Publication Date	Name of Applicant or Patentee
Bio		6,108,004	August 22, 2000	Medl
ik p		6,278,977 B1	August 21, 2001	Agrawal et al.
1510		6,286,005 B1	September 4, 2001	Cannon
550		6,349,290 B1	February 19, 2002	Horowitz et al.
•				
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				JUN 2 3 2004
				Technology Center 2100

EXAMINER SIGNATURE: Sh	- Que	W	DATE CONSIDERED:	04/25/05

<sup>\*</sup> Examiner: Initial if reference considered, whether or not in conformance with MPEP 609. Draw line through cite if not in conformance and not considered. Include copy of this form with next communication to applicant.

GLM/CAJ:kaa 05/11/05 6115-58351-01 373314

## Attorney Docket Number 6115-58351-01 Application Number 09/925,125 INFORMATION DISCLOSURE STATEMENT BY APPLICANT Filing Date August 9, 2001 First Named Inventor Scheurich Art Unit 2162 Examiner Name Baoquoc N. To

## U.S. PATENT DOCUMENTS

Copies of U.S. Patent documents do not need to be provided, unless requested by the Patent and Trademark Office. For patents, provide the patent number and the issue date. For published U.S. applications, provide the publication number and the publication date. For unpublished pending patent applications, provide the application number and the filing date.

Examiner's Inittals*	Cite No. (optional)	Namber	Publication Date	Name of Applicant or Patentee
Bo		5,119,318	06-1992	Paradies et al.
Bão		5,311,562	05-1994	Palusamy et al.
BTo		6,345,259	02-2002	Sandoval
No		6,430,545	08-2002	Honarvar et al.
No		6,499,023	12-2002	Dong et al.
1550		6,581,054	06-2003	Bogrett
OSTO		2002/0091636	07-2002	Bullard et al.
Blo		2002/0099598	07-2002	Eicher et al.
1550	-	2002/0133368	09-2002	Strutt et al.
150		2002/0165727	11-2002	Greene et al.
050	·	2002/0174000	11-2002	Katz et al.
		·		

EXAMINER SIGNATURE: B	f I	ATE ONSIDERED:	7/15/	US
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\* Examiner: Initial if reference considered, whether or not in conformance with MPEP 609. Draw line through cite if not in conformance and not considered. Include copy of this form with next communication to applicant.